

12. (New) A method as in claim 11 wherein said second shape is formed relative to the shape of a reference surface.

13. (New) A method as in claim 12 wherein said reference surface is located on a device to be tested.

14. (New) A method as in claim 12 further comprising:  
rotating the substrate about an axis passing substantially through a plane defined by the contact portions of the plurality of contact elements.

15. (New) A method as in claim 11 wherein said deformation of the substrate is performed manually.

16. (New) A method as in claim 11 wherein said deformation of the substrate is performed automatically.

17. (New) A method as in claim 13 wherein said device to be tested is one of a semiconductor wafer, a printed wiring substrate, a component of a printed wiring substrate, and a singulated semiconductor device.

18. (New) A method as in claim 11 wherein the substrate is one of a ceramic substrate, an organic substrate, a silicon wafer, and a metallic substrate.

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19. (New) A method as in claim 11 wherein the plurality of contact elements is couplable to an automated test system.

20. (New) A method as in claim 12 further comprising tilting the substrate to facilitate forming said second shape relative to the shape of said reference surface.

21. (New) A method of adjusting the surfaces of a plurality of substrates, each of the surfaces defined by contact portions of a plurality of contact elements disposed against a substrate of the plurality of substrates, the method comprising:

applying a force to at least one substrate in the plurality of substrates to deform the substrate and change the shape of the surface of the substrate such that a first set of surface shapes is changed to a second set of surface shapes;

adjusting the surfaces relative to one another to define a collective surface shape.

22. (New) A method as in claim 21 wherein said collective surface shape is formed relative to the shape of a reference surface.

23. (New) A method as in claim 22 wherein said reference surface is located on a device to be tested.

24. (New) A method as in claim 21 further comprising:

rotating at least one substrate of the plurality of substrates about an axis passing substantially through a plane defined by the contact portions of the plurality of contact elements.

25. (New) A method as in claim 21 further comprising:

rotating at least one substrate of the plurality of substrates about an axis substantially perpendicular to a plane defined by the contact portions of the plurality of contact elements.

26. (New) A method as in claim 21 further comprising:  
translating at least one substrate of the plurality of substrates substantially  
along a plane defined by the contact portions of the plurality of contact elements.
27. (New) A method as in claim 21 further comprising:  
translating at least one substrate of the plurality of substrates substantially  
perpendicularly to a plane defined by the contact portions of the plurality of contact  
elements.

#### REMARKS

Applicants note that no new matter has been added by way of this Preliminary Amendment. Applicants respectfully request consideration of the instant application as amended.

Please charge any insufficiency or credit any overpayment to Deposit Account No. 02-2666.

Respectfully submitted,

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Dated: 5/8/00

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